

SEMICONDUCTOR TM

KSE3055T

General Purpose and Switching Applications

- DC Current Gain Specified to I_C =10A
 High Current Gain-Bandwidth Product : f_T = 2MHz (Min.)



1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

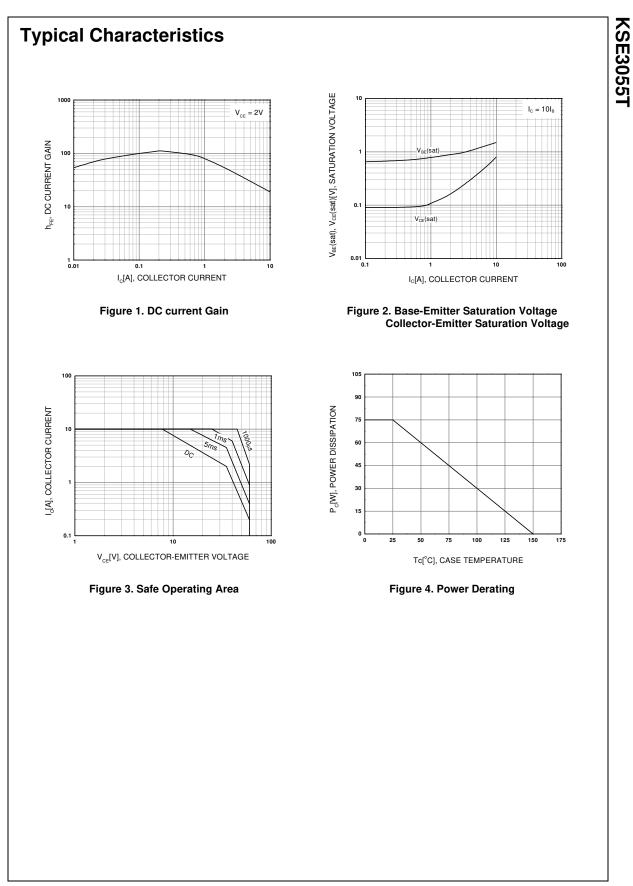
A	bsol	ute	Maximu	im Ratings	S T _C =25°C	unless otherwise noted
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Symbol	Parameter	Value	Units	
V _{CBO}	Collector -Base Voltage	70	V	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current	10	А	
I _B	Base Current	6	А	
P _C	Collector Dissipation (T _C =25°C)	75	W	
	Collector Dissipation (T _a =25°C)	0.6	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 ~ 150	°C	

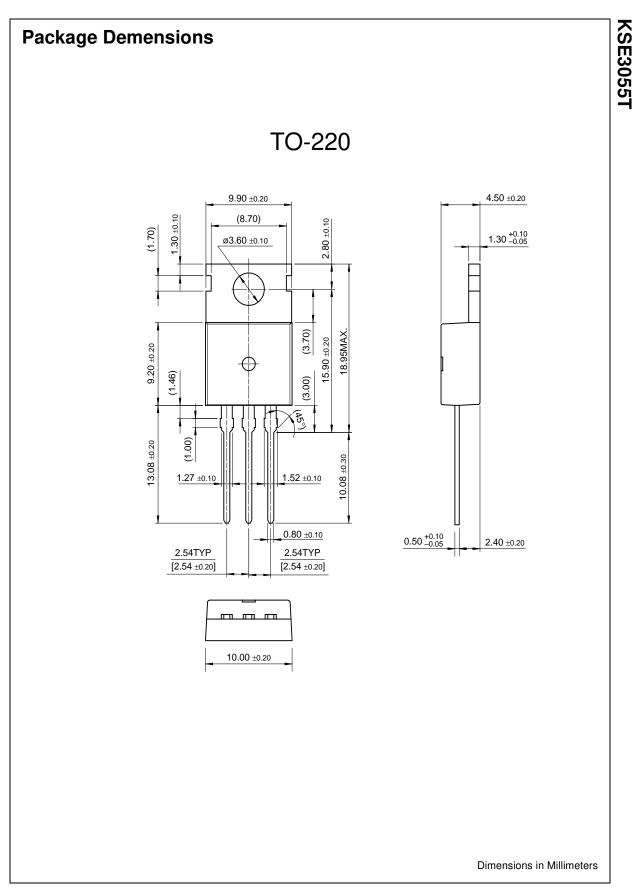
Electrical Characteristics $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 200 {\rm mA}, \ I_{\rm B} = 0$	60		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_B = 0$		700	μΑ
I _{CEX1} I _{CEX2}	Collector Cut-off Current	$V_{CE} = 70V, V_{BE}(off) = -1.5V$ $V_{CE} = 70V, V_{BE}(off) = -1.5V$ @ T _C = 150°C		1 5	mA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		5	mA
h _{FE}	*DC Current Gain	$V_{CE} = 4V, I_C = 4A$ $V_{CE} = 4V, I_C = 10A$	20 5	100	
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_{C} = 4A, I_{B} = 0.4A$ $I_{C} = 10A, I_{B} = 3.3A$		1.1 8	V V
V _{BE} (on)	*Base-Emitter On Voltage	$V_{CE} = 4V, I_C = 4A$		1.8	V
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 500mA	2		MHz

* Pulse test: PW≤300µs, duty cycle≤2% Pulse



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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSE3055T	Full Production	\$0.353	TO-220	3	BULK
KSE3055TTU	Full Production	\$0.353	TO-220	3	RAIL

* 1,000 piece Budgetary Pricing

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company

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